

# QPA4263A

DC to 3500MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

The QPA4263A is a high performance SiGe HBT MMIC amplifier. A Darlington configuration provides high  $F_T$  and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

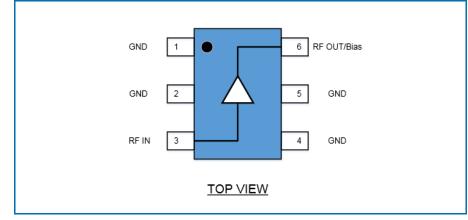


SOT-363 Package

### **Features**

- DC to 3500MHz Operation
- Cascadable 50Ω
- Single Voltage Supply
- Low Thermal Resistance Package

### Functional Block Diagram



# Applications

- Power Amplifier Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF/RF Buffer Amplifier
- Wireless Data, Satellite

### **Ordering Information**

QPA4263ASQ	Sample Bag with 25 pieces
QPA4263ASR	7" Reel with 100 pieces
QPA4263ATR7	7" Reel with 3000 pieces
QPA4263APCK401	850MHz, +8V Operation PCBA with 5-piece Sample Bag

Revision DS20160210 © 2016 Qorvo, Inc.

# QPA4263A

# **Absolute Maximum Ratings**

Parameter	Rating	Units
Device Voltage(V <sub>D</sub> )	+5.0	V
Device Current (ID)	90	mA
RF Input Power Note 1	+18	dBm
Storage Temperature	-55 to +150	°C
ESD Rating (HBM)	TBD	-
Moisture Sensitivity Level	MSL1	-

Notes:

- 1. Load Condition 1:  $Z_L = 50 \Omega$
- Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in this table.
- 3. Bias Conditions should also satisfy the following expression:  $I_DV_D$  <(T\_J -T\_L)/  $R_{TH},$  and  $T_L$  =T\_LEAD.

# **Recommended Operating Conditions**

Parameter		Units			
Falameter	Min	Тур	Max	Units	
Operating Temperature Range	-40		+105	°C	
Junction Temperature (TJ)			+125	°C	
Device Operating Voltage	+2.9	+3.2	+3.5	V	

### **Electrical Specifications – General**

Devementer	Specification		Units	Conditions		
Parameter	Min	Тур	Max	Units	Conditions	
		13.5		dB	850MHz	
Small Signal Gain, S21		12.3		dB	1950MHz	
		11.8		dB	2400MHz	
		+14.5		dBm	850MHz	
Output Power at 1 dB Compression		+14.1		dBm	1950MHz	
		+14.1		dBm	2400MHz	
		+31.8		dBm	850MHz	
Output Third Order Intercept Point		+29.2		dBm	1950MHz	
		+27.9		dBm	2400MHz	
		19.0		dB	850MHz	
Input Return Loss, S11		15.5		dB	1950MHz	
		16.2		dB	2400MHz	
		25.7		dB	850MHz	
Output Return Loss, S22		13.3		dB	1950MHz	
		13.0		dB	2400MHz	
•	<sub>0</sub> = + 3.2 V, \ <sub>BIAS</sub> = 110Ω,				P3 Tone Spacing=1 MHz, $P_{OUT}$ per tone = -5 dBm,	

# rfmd 🔪 QOUVO

### RFMD + TriQuint = Qorvo



Caution! ESD sensitive device.



RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional - operation of the device under Absolute Maximum Rating conditions is not implied.



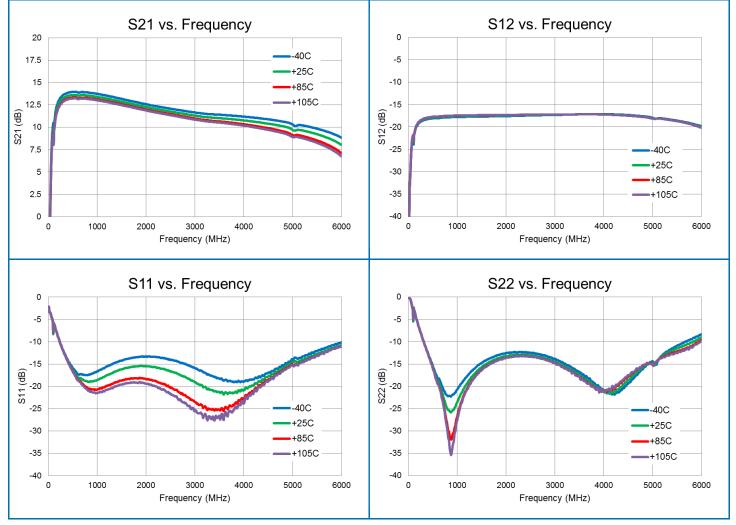


# QPA4263A

# **Electrical Specifications – General (Continued)**

Parameter	Specification		Units	Conditions	
	Min	Тур	Мах	Units	Conditions
		17.7		dB	850MHz
Reverse Isolation, S12		17.5		dB	1950MHz
		17.4		dB	2400MHz
		3.5		dB	850MHz
Noise Figure		3.7		dB	1950MHz
		3.9		dB	2400MHz
Thermal Resistance		105		°C/W	
Device Operating Current		45.0		mA	
Test Conditions unless otherwise specified: $V_D = +3.2 \text{ V}, V_S = +8 \text{ V}, I_D = 45 \text{ mA Typ.}, \text{ OIP3 Tone Spacing=1 MHz}, P_{OUT} \text{ per tone} = -5 \text{ dBm}, R_{BIAS} = 110\Omega, T_L = +25^{\circ}\text{C}, Z_S = Z_L = 50 \Omega$					

# **Typical Performance Using 850MHz Application Circuit**

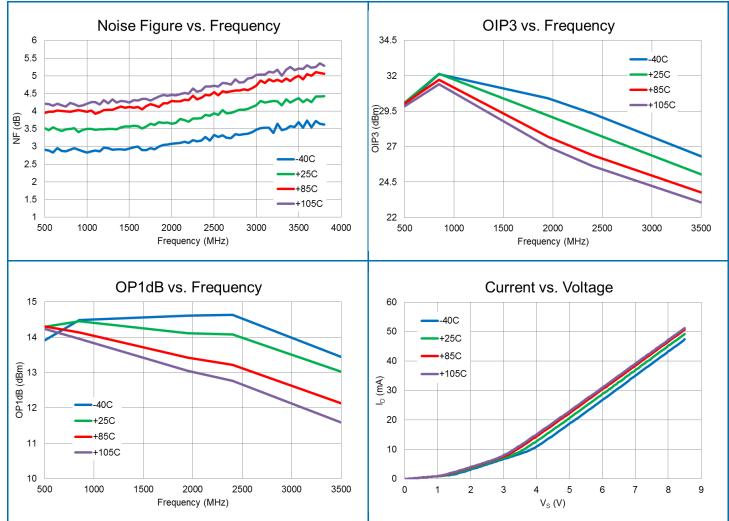


Revision DS20160210 © 2016 Qorvo, Inc. Disclaimer: Subject to change without notice www.rfmd.com / www.qorvo.com



# QPA4263A



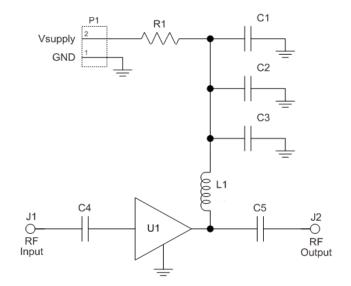




# QPA4263A

### **Evaluation Board and Schematic**





# **Evaluation Board Bill of Materials For 850MHz Application Circuit**

Description	Reference Designator	Manufacturer	Manufacturer's P/N
Gain Block	U1	QORVO	QPA4263A
РСВ	NA	Viasystems Technologies Corp	QPAXX63X-410(A)
CAP, 1uF, 10%, 25V, X7R, 1206	C1	Murata Electronics	GRM31MR71E105KA01L
CAP, 1000pF, 10%, 50V, X7R, 0402	C2	Murata Electronics	GRM155R71H102KA01D
CAP, 68pF, 5%, 50V, C0G, 0402	C3	Murata Electronics	GRM1555C1H680JA01D
CAP, 100pF, 5%, 50V, C0G, 0402	C4, C5	Murata Electronics	GRM1555C1H101JA01D
RES, 110 OHM, 5%, 1/2W, 1210	R1	Panasonic Industrial Devices	ERJ-14YJ111U
IND, 33nH, 5%, M/L, 0603	L1	Murata Electronics	LL1608-FSL33NJ
CONN, SMA, EL, FLT, 0.068" SPE-000318	J1. J2	Amphenol RF Asia Corp	901-10426
CONN, HDR, ST, 1x2, 0.100", HI-TEMP, T/H	P1	Samtec Inc.	HTSW-102-07-G-S

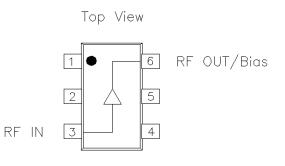


# QPA4263A

# **Component Values For Specific Frequency and Voltage in Application Circuit**

Reference	Frequency (MHz)							
Designator	500	850	1950	2400	3500			
C <sub>4</sub> , C <sub>5</sub>	220pF	100pF	68pF	56pF	39pF			
C <sub>3</sub>	100pF	68pF 22pF		22pF	15pF			
L <sub>1</sub>	68nH	33nH	22nH	18nH	15nH			
Required Bias Resistance for $I_D = 45mA$ Bias Resistance = $R_{BIAS} + R_{LDC} = (V_S - V_D) / I_D$								
Supply Vol	tage (Vs)	+6 V	+8 V	+10 V	+12 V			
Bias Resistanc	<b>ce</b> (R <sub>1 =</sub> R <sub>Bias</sub> )	62 Ω	110 Ω	150 Ω	200 Ω			
Note: Bias resistor improves current stability over temperature								

# **Pin Configuration and Description**



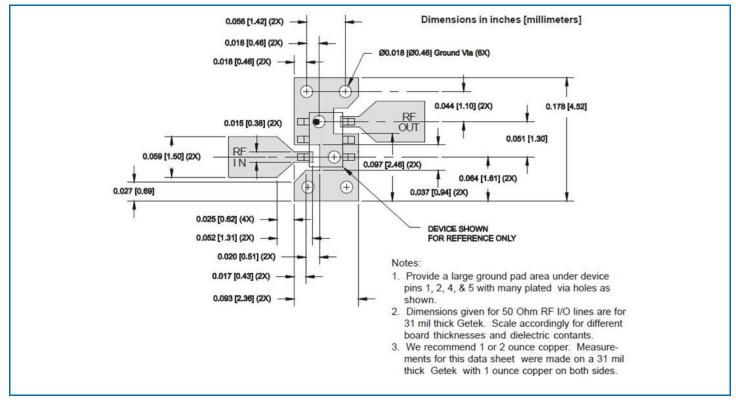
Pin	Label	Description
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the application schematic.
1, 2, 4, 5	GND	Connect to ground per application circuit drawing. For best performance, vias should be used as shown in the recommended pad layout.
6	RF OUT/BIAS	RF output and bias pin. Bias will be supplied to this pin through an external RF choke. A DC blocking capacitor is necessary on the RF output as shown in the application circuit.



# QPA4263A

# Package Marking

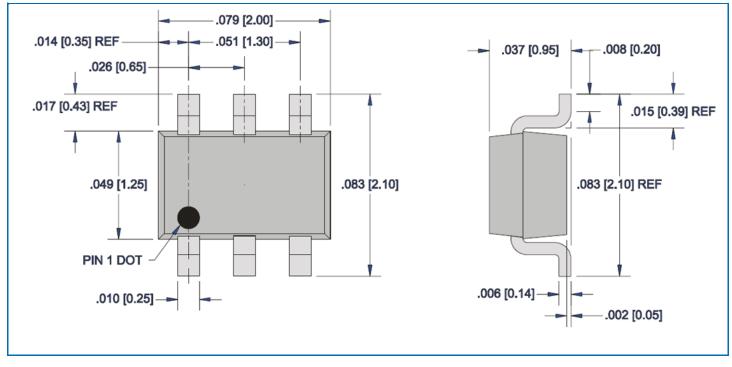
# Suggested Pad Layout (Dimensions in inches [millimeters])





# QPA4263A

Package Outline (Dimensions in inches [millimeters])



### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.rfmd.com Tel: 1-844-890-8163 Email: customer.support@gorvo.com

For information about the merger of RFMD and TriQuint as Qorvo:

Web: www.qorvo.com

### **Important Notice**

The information contained herein is believed to be reliable. RFMD makes no warranties regarding the information contained herein. RFMD assumes no responsibility or liability whatsoever for any of the information contained herein. RFMD assumes no responsibility or liability whatsoever for the use of the information contained herein. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the user. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for RFMD products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information.

RFMD products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.